0.2 A very low V_F MEGA Schottky barrier rectifiers

Rev. 01 — 24 November 2006

Produ

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in ultra small and flat lead Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package		Configuration
	NXP	JEITA	
PMEG6002EB	SOD523	SC-79	single
PMEG6002TV	SOT666	-	dual isolated

1.2 Features

Forward current: I_F ≤ 0.2 A

Reverse voltage: V_R ≤ 60 V

Very low forward voltage

Ultra small and flat lead SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. **Quick reference data**

Parameter	Conditions	Min	Тур	Max	Unit
forward current	$T_{amb} \le 25 ^{\circ}C$	-	-	0.2	Α
reverse voltage		-	-	60	V
forward voltage	I _F = 200 mA	1 -	540	600	mV
	reverse voltage	reverse voltage	reverse voltage -	reverse voltage	reverse voltage 60

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
SOD523			
1	cathode	[1]	
2	anode	1 2	1] [2
			sym001
SOT666			
1	anode (diode 1)		
2	not connected	6 5 4	6 5 4
3	cathode (diode 2)		
4	anode (diode 2)		
5	not connected	1 2 3	1 2 3 <i>006aaa440</i>
6	cathode (diode 1)	1 2 3	

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	Package			
	Name	Description	Version	
PMEG6002EB	SC-79	plastic surface-mounted package; 2 leads	SOD523	
PMEG6002TV	-	plastic surface-mounted package; 6 leads	SOT666	

4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG6002EB	B2
PMEG6002TV	1B

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V_R	reverse voltage		-	60	V
l _F	forward current	T _{amb} ≤ 25 °C	-	0.2	Α
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	2	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[1] -	2.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	PMEG6002EB		<u>[1]</u> _	300	mW
	PMEG6002TV		<u>[1]</u> _	200	mW
			[2] _	300	mW
Per devic	е				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	PMEG6002TV		[1] -	300	mW
			[2] _	400	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

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6. Thermal characteristics

Table 7 Thermal characteristics

Table 1.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PMEG6002EB		[1][2]	-	400	K/W
	PMEG6002TV		[1][2]	-	416	K/W
			[1][3]	-	318	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[4]</u>			
	PMEG6002EB		-	-	75	K/W
	PMEG6002TV		-	-	195	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

7. Characteristics

Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

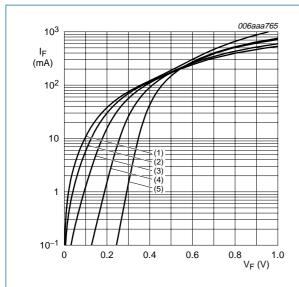
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diod	е					
V _F	forward voltage		<u>[1]</u>			
	er diode F forward voltage	I _F = 0.1 mA	-	130	170	mV
		I _F = 1 mA	-	190	230	mV
		I _F = 10 mA	-	260	300	mV
		I _F = 100 mA	-	420	470	mV
		$I_F = 200 \text{ mA}$	-	540	600	mV
I_R	reverse current					
		V _R = 10 V	-	2	10	μΑ
		V _R = 60 V	-	20	100	μΑ
		V _R = 10 V; T _{amb} = 100 °C	-	310	-	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	14	20	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

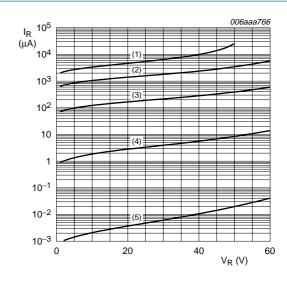
^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[4] Soldering point of cathode tab.



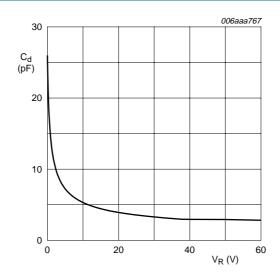
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
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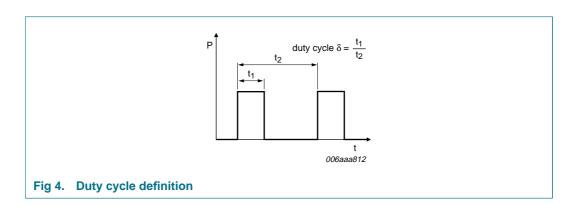
Fig 2. Reverse current as a function of reverse voltage; typical values



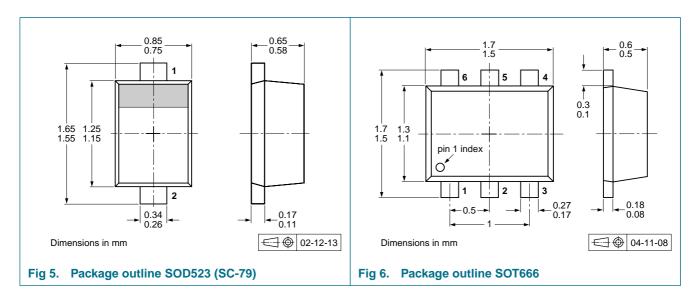
 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$

Fig 3. Diode capacitance as a function of reverse voltage; typical values

8. Test information



9. Package outline



10. Packing information

Table 9. Packing methods

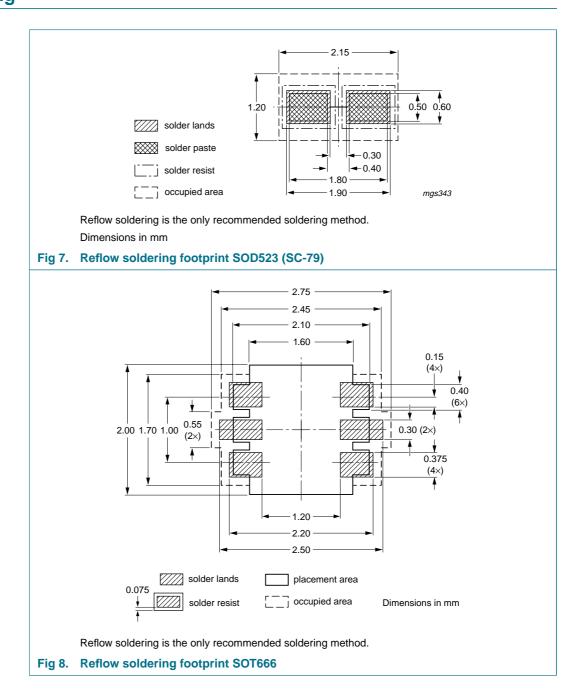
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packin	ıg quant	ity	
			3000	4000	8000	10000
PMEG6002EB	SOD523	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-115	-	-	-135
PMEG6002TV	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-

^[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6002EB_PMEG6002TV_1	20061124	Product data sheet	-	-

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13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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PMEG6002EB; PMEG6002TV

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